

Abstract of the Disclosure:

The novel etching process for a two-layer metallization, or dual damascene patterning, is simple and cost-effective to carry out and reliably prevents fences from forming during the 5 etching process in the region of the polymer intermediate layer. The etching of the oxide layer and of the polymer intermediate layer for the dual damascene patterning is effected by a CF₄ ARC open process with high selectivity with respect to the photoresist with a lengthened etching time.

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